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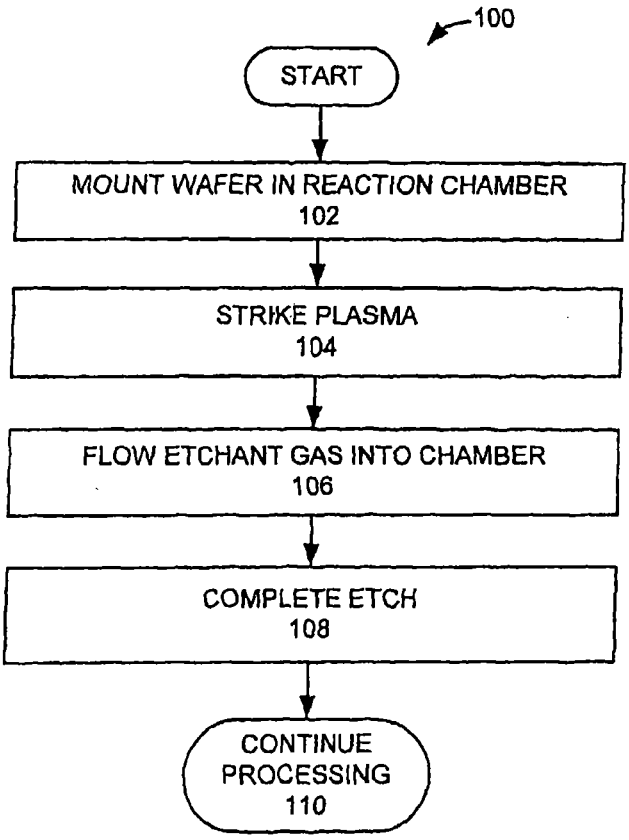
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(54) Title: USE OF HYDROCARBON ADDITION FOR THE ELIMINATION OF MICROMASKING DURING ETCHING OF ORGANIC LOW-K DIELECTRICS



(57) Abstract: A method for etching features in an integrated circuit wafer, the wafer incorporating at least one dielectric layer is provided. Generally, the wafer is disposed within a reaction chamber. An etchant gas comprising a hydrocarbon additive and an active etchant is flowed into the reaction chamber. A plasma is formed from the etchant gas within the reaction chamber. The feature is etched in at least a portion of the dielectric layer. Several sources of appropriate hydrocarbon are identified as suitable to practice the present invention. These include, but are specifically not limited to: ethylene, C_2H_4; ethane, C_2H_6; and methane, CH_4.

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